Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 23-Aug-99
		ADC (8-bit)											
	Note: Entries in **RED** indicate data added since the 1997 Compendium.												
GSFC	7820RP/372		LCCMOS (Seiko 0820 die)	MPS					Jul-94	>80			LaBel
GSFC	**AD570**	**Sucessive Approximation**	**CMOS**	**ADI**	**7**	**3.0E-04**			**1996**	**>52.5**		**BNL**	**LaBel, et al, 97IEEE Wrkshp Rec., pg 14.**
BREL	AD7824		CMOS	ADI	<<5	1.0E-04			Feb-91				Fluorine only
ARSP	AD9048	Flash	Bipolar	ADI	<1	3.0E-04			1994				Koga, 94IEEE TNS, No. 6, pg 2172. D/C 9146. Fail to 2's complement @ LET = 8; 1.5E-05 cm2.
HON	AD9048TQ	Flash	Bipolar	ADI	<<3	3.2E-04							Fail LET = 7; 1.3E-05 cm^2. Unexplained high currents
JPL	**HI1276**	**Flash**	**ECL (Bipolar)**	**HAR**					**Mar-97**	**>70**		**BNL**	**Temp. increased from ~32° C to 69° C during test.**
JPL	HI1276	Flash	Bipolar- ECL	HAR					Mar-97	>70		BNL	With self heating up to T = 69 °C.
HON	HS9008RH	Flash	CMOS	HAR	~15	2.0E-05			1994	>150			Sexton, et al, 94IEEE Wrkshp Rec., pg 55. Up to T = 125° C.
GD	MP7683	Flash	CMOS	MPS		4.0E-06							
SEI	**MP7684**	**20 MSPS**	**CMOS**	**EXR**	**<11.4**	**6.0E-02**			**1997**	**18 - 26.6**		**BNL**	**Layton, et al, 98IEEE Wrkshp Rec., pg 170.**
ARSP	MP7684		CMOS	MPS	~1	1.0E-03			Dec-91	>100			
JPL	MP7684	Flash	CMOS	MPS					Nov-92	>120			Up to 125° C.
JPL	MP7684A	Flash	CMOS	MPS					Nov-92	>120			Up to 125° C.
JPL	SPT7725	Flash	CMOS	SPT					Mar-97	>120		BNL	Used thermo-electric cooler to maintain temp < 34 °C.
ARSP	TDC1048		Bipolar hybrid	TRW	2	2.0E-03			Apr-93	>95			D/C 8540
JPL	TDC1048J6A		Bipolar hybrid	TRW	~5				Nov-89	>95			T=96° C. Same SEU as adjacent part.
JPL	TDC1048J6C		Bipolar hybrid	TRW	~5				Nov-89	>95			T=96° C. Same SEU as adjacent part.
NRL	TMC1175	Flash	CMOS	TRW					Feb-93	<<29.5	2.0E+04	BNL	Limited LU test. Stapor memo.
JPL	**TMC1175C3V20**	**Video Flash**	**Submicron CMOS**	**RAY**					**Jun-97**	**25**	**1.1E-04**	**BNL**	**LU rate (GCR) = 5E-03/yr.**
CNES	TMS8338		CMOS (HS13)	TMS					Aug-91	~20	5.0E-04		See following entry.
CNES	TMS8338		CMOS (HCMOS3)	TMS					Aug-91	~12	2.0E-03		See preceding entry.

Heavy Ion SEE

Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 23-Aug-99
Legend													
	Manufacturers: ADI - Analog Devices, Inc; Har - Harris Corp; EXR - Exar Corp; MPS - Micro Power Systems; RAY - Raytheon; SPT - Signal Processing Technologies; TMS - Thomson Military & Space, France; TRW - TRW Systems.												
	Test Organizations			**Radiation Test Facilities**									
	ARSP - Aerospace Corp., El Segundo, CA			BNL - Tandem Van de Graaff, Brookhaven National Laboratories, Long Island, NY									
	BREL - Boeing Radiation Effects Laboratory, Seattle, WA												
	CNES - Centre National d'etudes Spatiales, Toulouse, France												
	GD - General Dynamics, San Diego, CA												
	GSFC - Goddard Space Flight Center, Greenbelt, MD												
	HON - Honeywell Space Systems, Clearwater, FL												
	JPL - Jet Propulsion Laboratory, Pasadena, CA												
	SEI - Space Electronics, Inc												